App No.: 10/812,412 Docket No.: 5438 Inventor: Steven WANG et al.
Title: METHOD FOR PRODUCING A DEEP TRENCH CAPACITOR IN A SEMICONDUCTOR SUBSTRATE

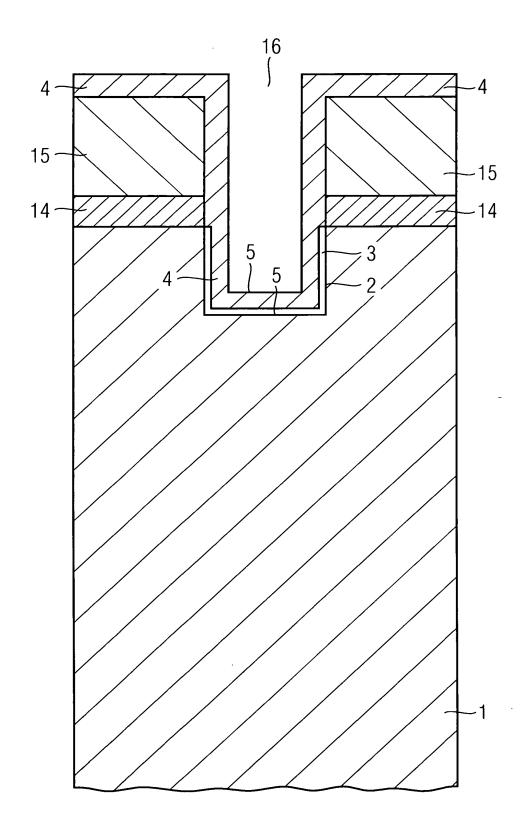
1/13

Sheet 1 of 13

Docket No.: 543822005300



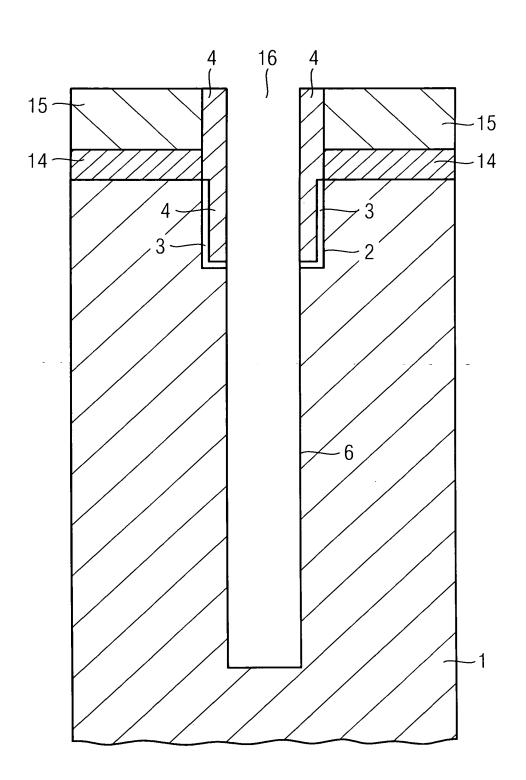
FIG 1A



App No.: 10/812,412
Inventor: Steven WANG et al.
Title: METHOD FOR PRODUCING A DEEP TRENCH
CAPACITOR IN A SEMICONDUCTOR SUBSTRATE

2/13
Sheet 2 of 13

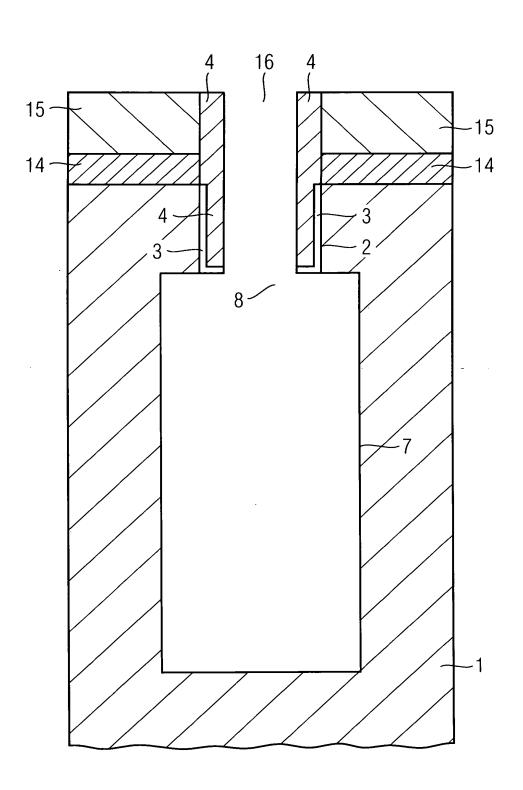
FIG 1B



App No.: 10/812,412
Inventor: Steven WANG et al.
Title: METHOD FOR PRODUCING A DEEP TRENCH
CAPACITOR IN A SEMICONDUCTOR SUBSTRATE

3/13
Sheet 3 of 13

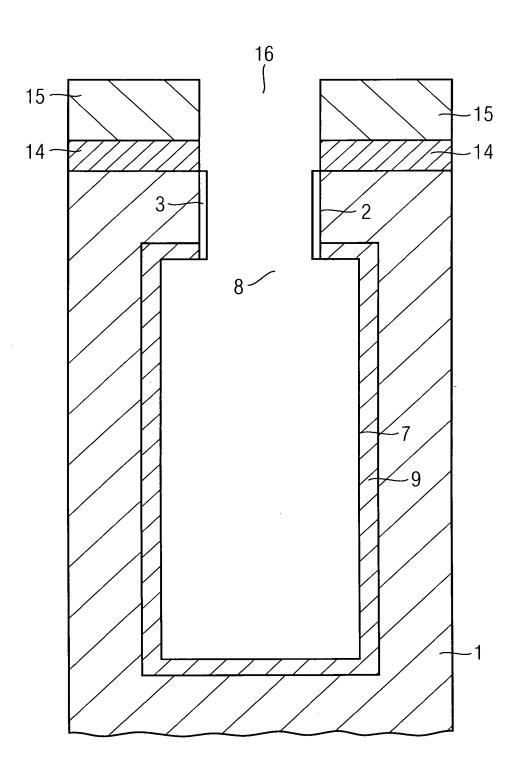
FIG 1C



App No.: 10/812,412
Inventor: Steven WANG et al.
Title: METHOD FOR PRODUCING A DEEP TRENCH
CAPACITOR IN A SEMICONDUCTOR SUBSTRATE

4/13
Sheet 4 of 13

FIG 1D

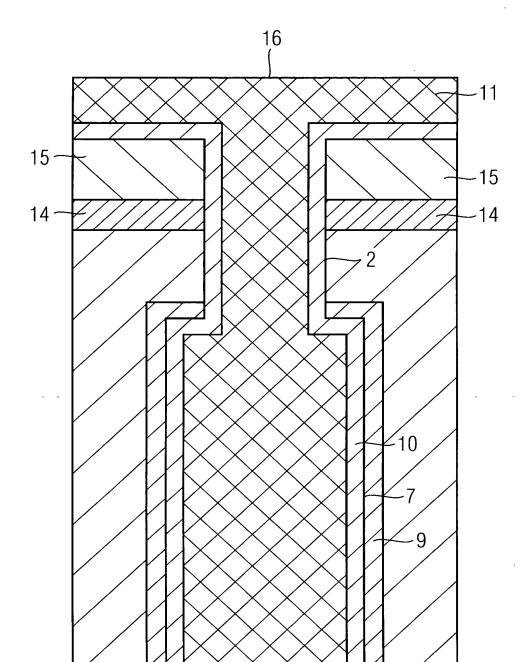


App No.: 10/812,412 Docket No.: 5438: Inventor: Steven WANG et al.
Title: METHOD FOR PRODUCING A DEEP TRENCH CAPACITOR IN A SEMICONDUCTOR SUBSTRATE Docket No.: 543822005300

5/13

Sheet 5 of 13

FIG 1E



App No.: 10/812,412 Inventor: Steven WANG et al.

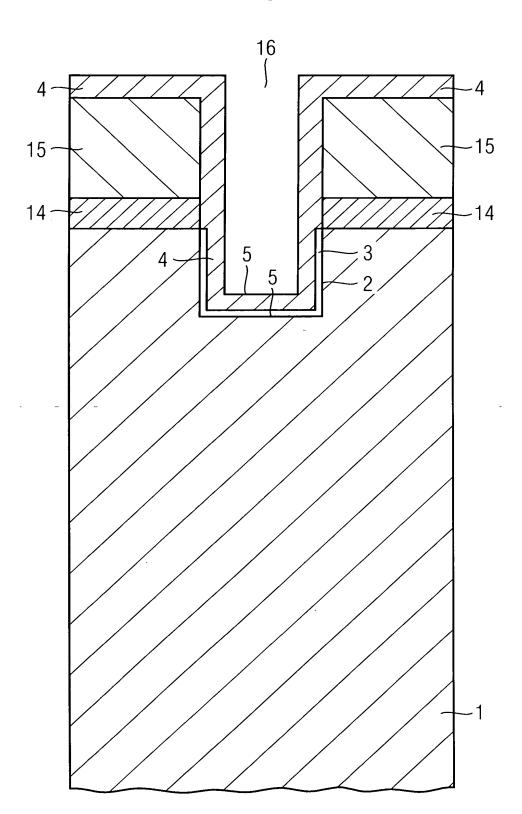
Docket No.: 54382200530

Title: METHOD FOR PRODUCING A DEEP TRENCH CAPACITOR IN A SEMICONDUCTOR SUBSTRATE

6/13

Sheet 6 of 13

FIG 2A

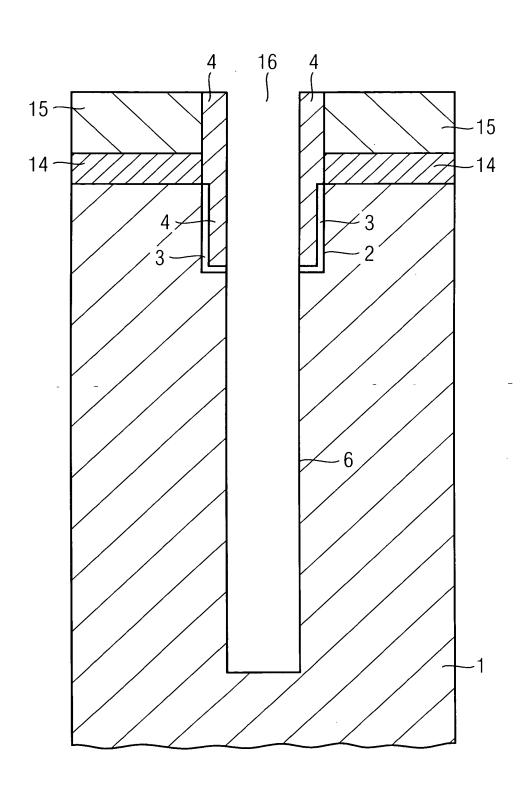


Docket No.: 543822005300

App No.: 10/812,412
Inventor: Steven WANG et al.
Title: METHOD FOR PRODUCING A DEEP TRENCH
CAPACITOR IN A SEMICONDUCTOR SUBSTRATE
7/13
She

Sheet 7 of 13

FIG 2B



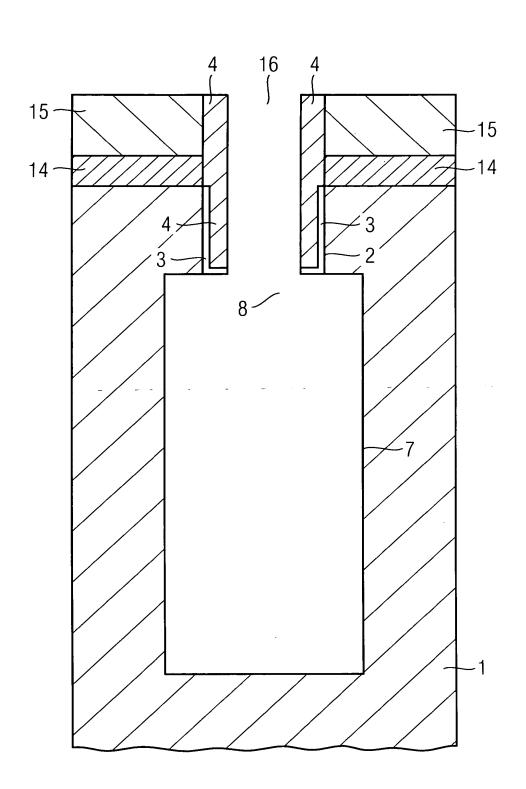
Docket No.: 54382200530

App No.: 10/812,412
Inventor: Steven WANG et al.
Title: METHOD FOR PRODUCING A DEEP TRENCH CAPACITOR IN A SEMICONDUCTOR SUBSTRATE

8/13
She

Sheet 8 of 13

FIG 2C



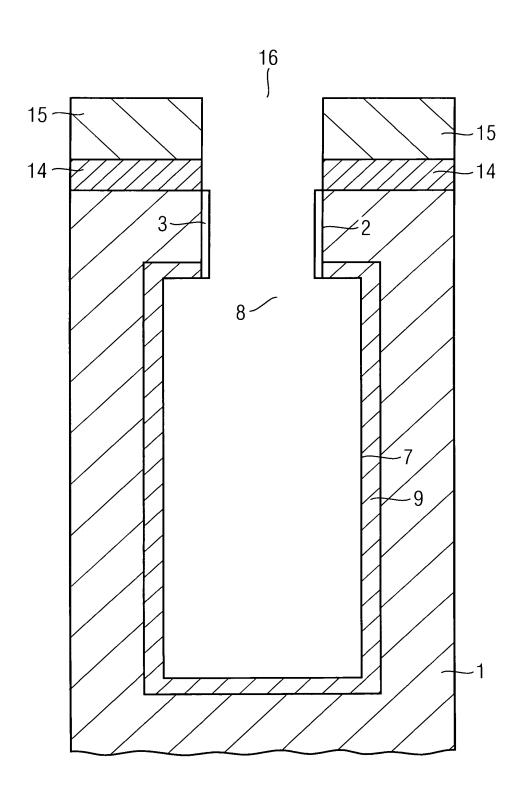
Docket No.: 543822005300

App No.: 10/812,412
Inventor: Steven WANG et al.
Title: METHOD FOR PRODUCING A DEEP TRENCH CAPACITOR IN A SEMICONDUCTOR SUBSTRATE

9/13
She

Sheet 9 of 13

FIG 2D



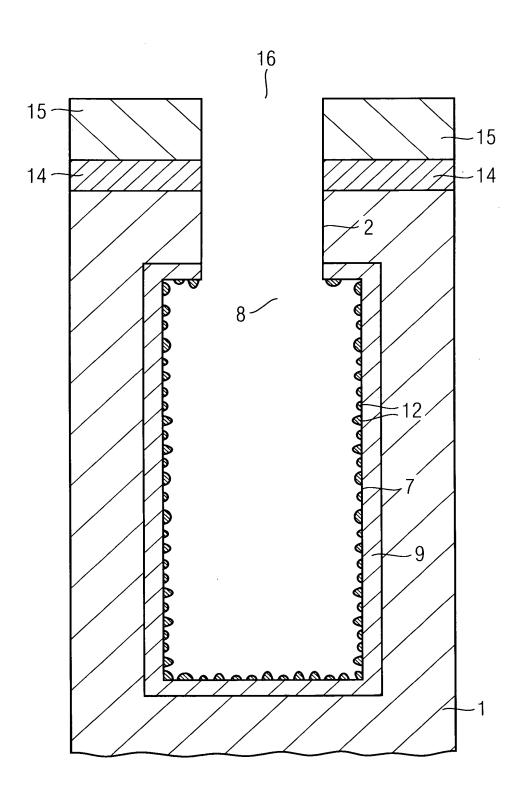
App No.: 10/812,412 Docket No.: 54382200530 Inventor: Steven WANG et al.

Title: METHOD FOR PRODUCING A DEEP TRENCH CAPACITOR IN A SEMICONDUCTOR SUBSTRATE

1 \(\text{1} \) \(1 \) \(2 \) Sheet 10 of 13

10/13

FIG 2E



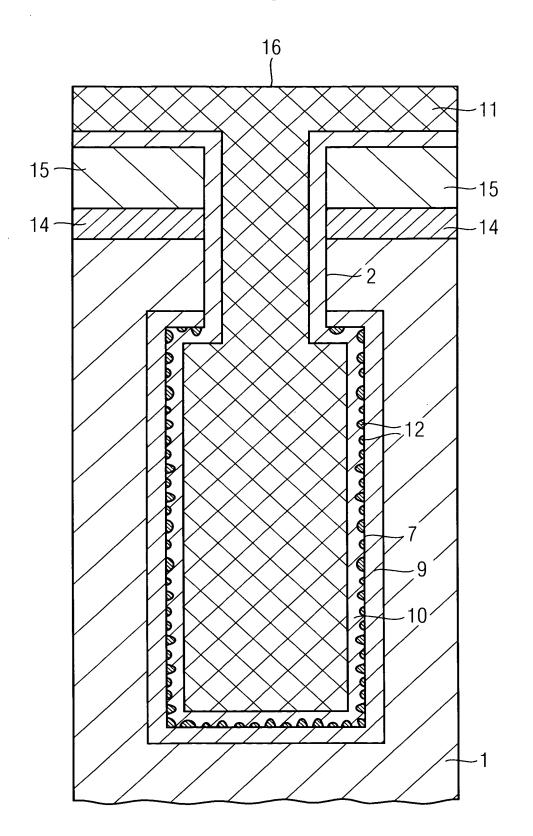
Docket No.: 543822005300

App No.: 10/812,412
Inventor: Steven WANG et al.
Title: METHOD FOR PRODUCING A DEEP TRENCH CAPACITOR IN A SEMICONDUCTOR SUBSTRATE

11/13
Shee

Sheet 11 of 13

FIG 2F



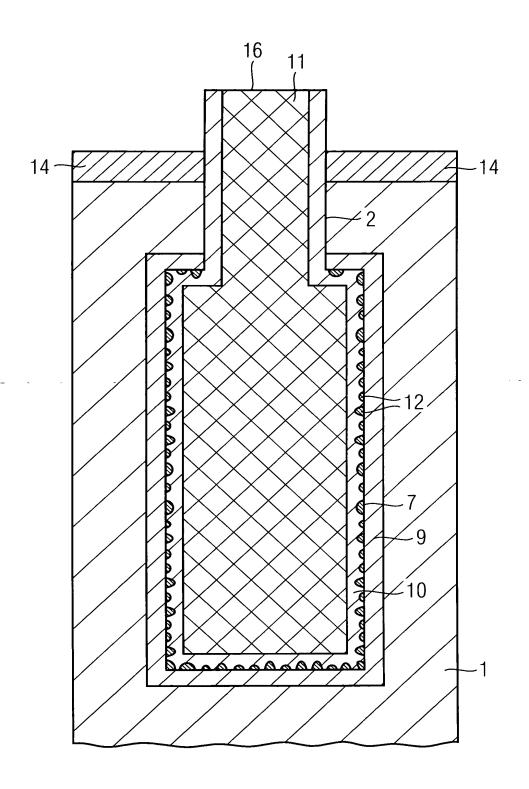
Docket No.: 54382200530

App No.: 10/812,412
Inventor: Steven WANG et al.
Title: METHOD FOR PRODUCING A DEEP TRENCH
CAPACITOR IN A SEMICONDUCTOR SUBSTRATE

12/13
Shee

Sheet 12 of 13

FIG 2G



App No.: 10/812,412 Docket No.: 543822005300 Inventor: Steven WANG et al.
Title: METHOD FOR PRODUCING A DEEP TRENCH CAPACITOR IN A SEMICONDUCTOR SUBSTRATE
12/12 Sheet 13 of 13

13/13

FIG 2H

